

Interference Search History Print out MT

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	(non-volatile near memory and substrate and trench and gate and source/drain and dielectric and charge-trapping near layer).CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/11/18 09:53